

1      **ABSTRACT OF THE DISCLOSURE**

2      In one aspect, the invention encompasses a semiconductor  
3      processing method. A layer of material is formed over a semiconductive  
4      wafer substrate. Some portions of the layer are exposed to energy  
5      while other portions are not exposed. The exposure to energy alters  
6      physical properties of the exposed portions relative to the unexposed  
7      portions. After the portions are exposed, the exposed and unexposed  
8      portions of the layer are subjected to common conditions. The common  
9      conditions are effective to remove the material and comprise a rate of  
10     removal that is influenced by the altered physical properties of the  
11     layer. The common conditions remove either the exposed or unexposed  
12     portions faster than the other of the exposed and unexposed portions.  
13     After the selective removal of the exposed or unexposed portions, and  
14     while the other of the exposed and unexposed portions remains over the  
15     substrate, the wafer is cut into separated die. In another aspect, the  
16     invention encompasses another semiconductor processing method. A  
17     layer of  $(CH_3)_ySi(OH)_{4-y}$  is formed over a substrate. Some portions of  
18     the layer are exposed to ultraviolet light while other portions are not  
19     exposed. The exposure to ultraviolet light converts the exposed portions  
20     to  $(CH_3)_xSiO_{2-x}$ . After the exposure to ultraviolet light, the exposed and  
21     unexposed portions of the layer are subjected to hydrofluoric acid to  
22     selectively remove the  $(CH_3)_ySi(OH)_{4-y}$  of the unexposed portions relative  
23     to the  $(CH_3)_xSiO_{2-x}$  of the exposed portions.